

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket Number (Optional) YOR919990281US3 (12795AB)		Application Number 10/691,299 Unassigned
	Applicant(s) Paul D. Agnello, et al.		
	Filing Date Herewith		Group Art Unit 2814 Unassigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
mbh		5,510,295	4/23/96	Cabral, Jr., et al.	148	016.147	
mbh		5,608,226	3/4/97	Yamada, et al.	250	492.2	
mbh		5,624,869	4/29/97	Agnello, et al.	257	E21.165	
mbh		5,828,131	10/27/98	Cabral, Jr., et al.	257	768	

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

mbh		M. Lawrence, et al.,(1991),"Growth of Epitaxial CoSi2 on (100)Si," Appl. Phys. Lett., Vol. 58, No. 12, pp. 1308-1310
mbh		C. Cabral, Jr., et al.,(1995),"In-Situ X Ray Diffractin and Resistivity Analysis of CoSi2 Phase Formation With and Without a Ti Interlayer at Rapid Thermal Annealing Rates," Mat. Res. Soc. Symp. Proc., Vol. 375, pp. 253-258.

EXAMINER <i>Muralin R. Hoff</i>	DATE CONSIDERED <i>11/23/05</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.